

# Dynamical polarization of doped graphene

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Electronic properties of graphene, Jan 07<sup>1</sup>

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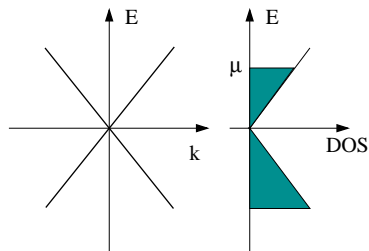
<sup>1</sup>New J. Phys. **8**, 318 (2006)

# Outline

- 1 RPA Polarization and dielectric function
- 2 Static screening
  - Friedel oscillations
  - RKKY interaction
- 3 Plasmon
- 4 Expectations for acoustical phonon

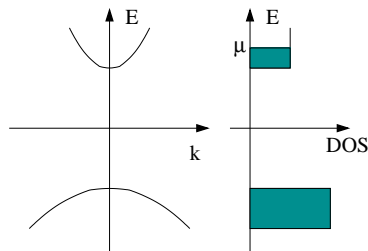
# Comparison with 2DEG

## Graphene



- $E(\mathbf{k}, \lambda) = \lambda \hbar \mathbf{v}_F \mathbf{k}$ , no gap
- $DOS(E) := 1/A \partial N / \partial E \propto E$
- Two valleys  $s$  and spinor wavefunction  $(A, B)$

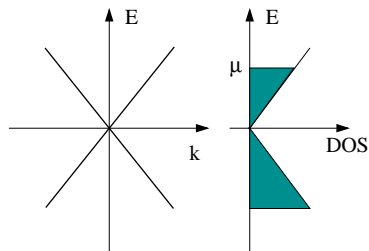
## 2DEG



- $E(\mathbf{k}, \lambda) = \frac{\hbar^2 \mathbf{k}^2}{2m^*}$ , gap (1.4 eV for GaAs)
- $DOS(E) = const$
- Eigenfunctions are plane waves

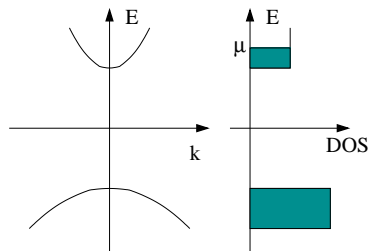
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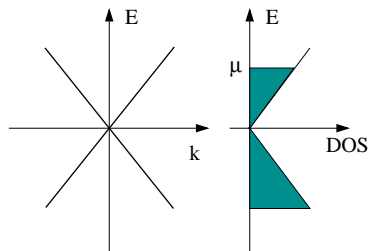
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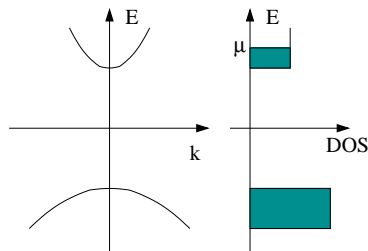
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# Dielectric function and polarization in linear response

Dielectric function  $\varepsilon(\mathbf{q}, \omega)$  and polarization  $\chi(\mathbf{q}, \omega)$  describe internal el-el interaction as well as screening of an external potential  $\phi_{\text{ext}}(\mathbf{q}, \omega)$ .

$$\phi_{\text{tot}}(\mathbf{q}, \omega) = \frac{\phi_{\text{ext}}(\mathbf{q}, \omega)}{\varepsilon(\mathbf{q}, \omega)}; \quad \rho_{\text{ind}}(\mathbf{q}, \omega) = -e \chi(\mathbf{q}, \omega) \phi_{\text{ext}}(\mathbf{q}, \omega)$$

$$\chi^0(\mathbf{q}, i\omega_n) = -\frac{1}{A} \int_0^\beta d\tau e^{i\omega_n \tau} \langle T \rho(\mathbf{q}, \tau) \rho(-\mathbf{q}, 0) \rangle$$

In RPA approximation electron-electron interaction treated self-consistently

$$\chi(\mathbf{q}, \omega) \approx \frac{\chi^0(\mathbf{q}, \omega)}{1 - v_q \chi^0(\mathbf{q}, \omega)} \Rightarrow \varepsilon(\mathbf{q}, \omega) \approx 1 - v_q \chi^0(\mathbf{q}, \omega)$$

$v_q$  is in-plane Coulomb potential.

# Mathematical expression

$$\chi^0(\mathbf{q}, i\omega_n) = \frac{g_S g_V}{(2\pi)^2} \int d^2k \sum_{\lambda, \lambda' = \pm} f^{\lambda \lambda'}(\mathbf{k}, \mathbf{q}) \frac{n_F(E^\lambda(\mathbf{k})) - n_F(E^{\lambda'}(\mathbf{k} + \mathbf{q}))}{E^\lambda(\mathbf{k}) - E^{\lambda'}(\mathbf{k} + \mathbf{q}) + i\hbar\omega_n}$$
$$f^{\lambda \lambda'}(\mathbf{k}, \mathbf{q}) = \frac{1}{2} \left( 1 + \lambda \lambda' \frac{\mathbf{k} + \mathbf{q} \cos \varphi}{|\mathbf{k} + \mathbf{q}|} \right)$$

- Summation over bonding and anti-bonding bands  $\lambda, \lambda'$ ,  
 $E^\lambda(\mathbf{k}) = \lambda \hbar v_F k$
- Wavefunction overlaps  $f^{\lambda \lambda'}(\mathbf{k}, \mathbf{q})$
- Linear energy dispersion  $E^\lambda(\mathbf{k}) = \lambda \hbar v_F k$

We calculate at zero temperature (i.e. we assume  $\mu/k_B \gg T$ ).

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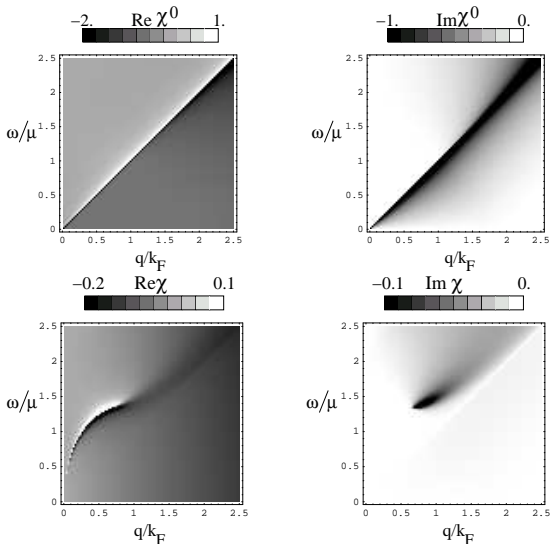
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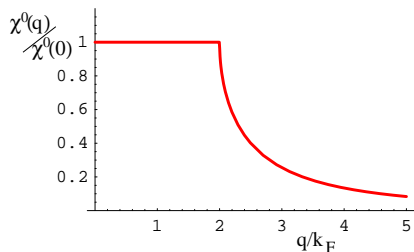
# General characteristics of RPA Polarization



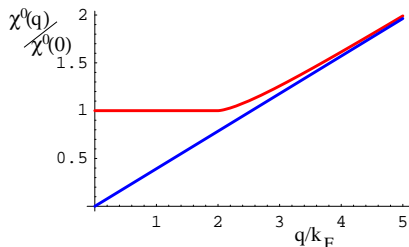
- Singularity of  $\chi^0(q, \omega)$  at limit of intraband SPE.
- Singularity of  $\chi(q, \omega)$  reflects plasmon

# Static polarization $\omega = 0$

## 2DEG



## Graphene

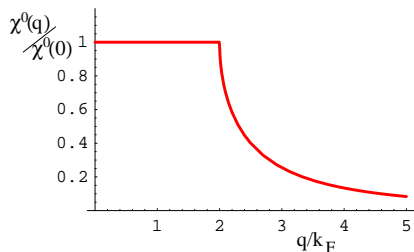


- Polarization is constant ( $-DOS(\mu)$ ) for  $q < 2k_F$ , however for  $q > 2k_F$  the polarization increases linear in  $q$  for graphene and falls off quadratically for the 2DEG.
- At  $q = 2k_F$  the polarization is non-analytical with a discontinuous second (first) derivative for graphene (2DEG).

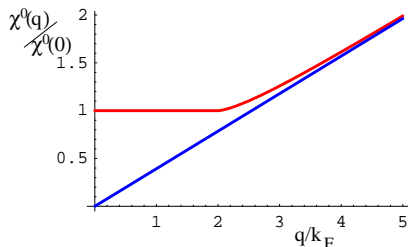
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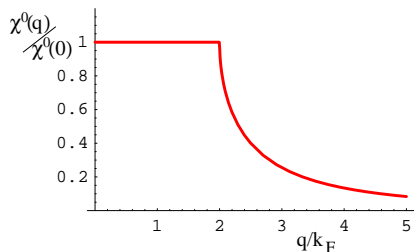


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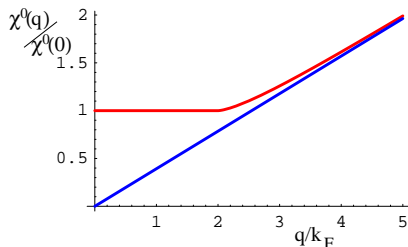
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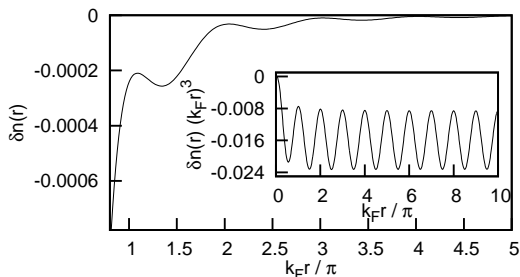
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# Screening of charged impurities in doped graphene



$$\delta n(r) = \frac{e}{(2\pi)^2} \int d^2q \left( \frac{1}{\epsilon(q,0)} - 1 \right) e^{i\mathbf{q}\cdot\mathbf{r}} = n_{TF}(r) + n_{osc}(r)$$

$$n_{TF}(r) \propto \frac{1}{k_F r^3}; \quad n_{osc}(r) \propto \frac{\cos(2k_F r)}{k_F r^3}; \quad n_{osc}^{2DEG}(r) \propto \frac{\cos(2k_F r)}{r^2}$$

In graphene  $n_{TF}(r) > n_{osc}(r)$ , so that  $\delta n(r)$  has always same sign.

V. V. Cheianov, V. Fal'ko PRL **97**, 226801 (2006).

# Screening of charged impurities in undoped graphene

- Static polarization is linear in  $q$ ,

$$\chi^0(q, 0) = -\frac{q}{4\hbar v_F}.$$

Since it is analytic, there is no oscillating contribution to the induced charge or potential.

- The static dielectric function is constant,

$$\varepsilon(q, 0) = 1 - v_q \chi^0(q, 0) = \text{const.}$$

The total potential and the total charge density are reduced by a constant with respect to the external ones.

- This screening behavior is typical for an insulator.

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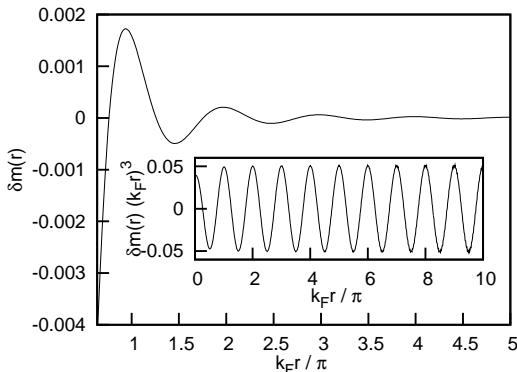


Effective interaction between magnetic imp. or induced spin density

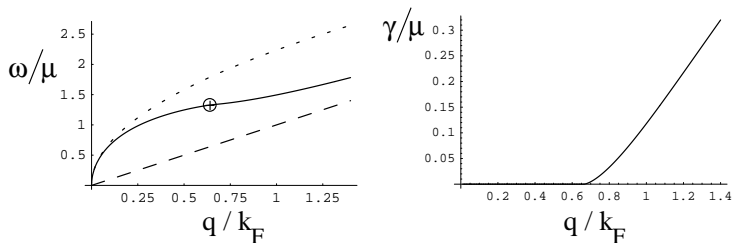
$$\begin{aligned}\delta m(\mathbf{r}) &\propto \chi^0(\mathbf{r}) \\ \delta m^{2DEG}(\mathbf{r}) &\sim \frac{\cos(2k_F r)}{r^2} \\ \delta m^{Graph}(\mathbf{r}) &\sim \frac{\cos(2k_F r)}{r^3}\end{aligned}$$

**However** if spin impurities replace single carbon atoms sublattice-symmetry is broken:  $\delta m^{Graph}(\mathbf{r}) \sim r^{-2}$

V. V. Cheianov, V. Fal'ko PRL **97**, 226801 (2006).



# Plasmon in graphene

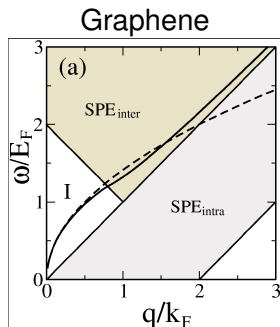
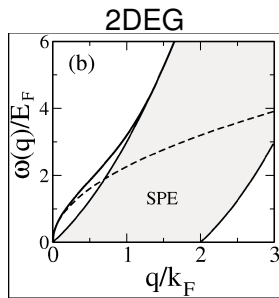


Dispersion  $\omega_P(q)$  and decay rate  $\gamma(\mathbf{q})$  determined by  $\varepsilon(q, \omega_P - i\gamma) = 0$ , with  $\varepsilon(q, \omega) = 1 - v_q \chi^0(q, \omega)$

- As in 2DEG we obtain for  $q \rightarrow 0$ :  $\omega_P^2(q) \propto \mu q$ .
- Different dependence on electron concentration since  $\mu \propto n^{1/2}$  ( $\mu \propto n$ ) in graphene (2DEG).<sup>2</sup>

<sup>2</sup>E. Hwang, S. Das Sarma, cond-mat/0610561

# Plasmons in 2DEG and in graphene

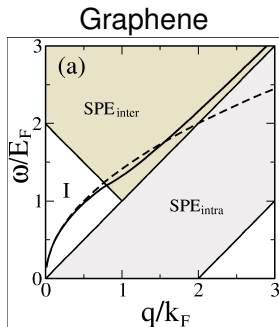
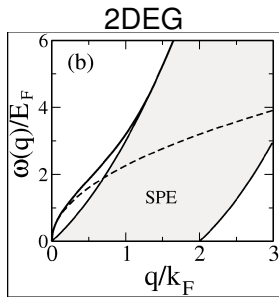


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- Damping due to interband excitations absent in 2DEG. Stability regime increases proportional to doping  $\mu$ . For  $\mu = T = 0$  plasmons are always unstable, however not at  $T > 0^3$

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# Acoustical phonons in graphene

- Screening of the ion-ion interaction by conduction electrons determines phonon dispersion.
- Following Ashcraft and Mermin phonon dispersion is estimated by:

$$\omega_{AP}^2(k) \sim \frac{\Omega_P^2(k)}{\epsilon(k)},$$

with  $\Omega_P(k)$  is ion plasma frequency

- For  $k \rightarrow 0$  one obtains  $\omega_{AP}(k) = v_S k$  with the sound velocity:  
In 2DEG:  $v_S \approx \sqrt{m/2M} v_F$  (Bohm-Staver relation).  
In graphene:  $v_S = v_F \sqrt{\frac{\pi E_0}{\mu}}$  with  $E_0 = \hbar^2 / MA_C \approx 0.1$  meV.

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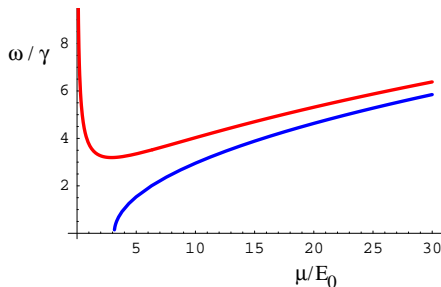
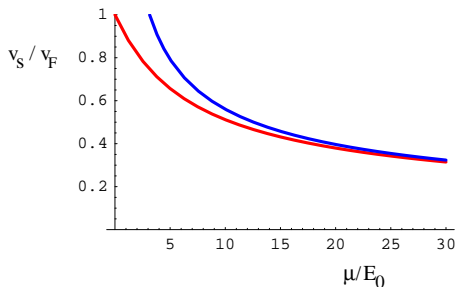
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# Acoustical phonons in graphene

Phonon dispersion and decay rate given by roots of  $\varepsilon_{\text{tot}}(\mathbf{k}, \omega + i\gamma)$  :

$$0 = \varepsilon_{\text{tot}}(\mathbf{k}, \omega) = \varepsilon_{\text{el}}(\mathbf{k}, \omega) + \varepsilon_{\text{ion}}(\mathbf{k}, \omega) - 1$$

with  $\varepsilon_{\text{ion}}(\mathbf{k}, \omega) = 1 - \frac{\Omega_P^2(\mathbf{k})}{\omega^2}$  dielectric function of ion plasma.





# Outlook and summary

- Analytic expression of RPA polarization at arbitrary  $k$  and  $\omega$ .
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# Minimal conductivity at Dirac point

Conductivity and polarization are related due to continuity equation/  
charge conservation

$$\begin{aligned}\operatorname{Re}(\sigma(\mathbf{q}, \omega)) &= -\frac{e^2 \omega}{q^2} \operatorname{Im}(\chi(\mathbf{q}, \omega)) \\ \sigma_0 &:= \lim_{\omega \rightarrow 0} \lim_{q \rightarrow 0} \operatorname{Re}(\sigma(\mathbf{q}, \omega)) = \frac{\pi}{2} \frac{e^2}{h}\end{aligned}$$

Finite conductivity at Dirac-point. Value of conductivity is unaffected by Coulomb interaction, since same result for  $\chi = \chi_0$  or  $\chi = \chi_0 / (1 - v_q \chi_0)$ . Small deviation from Landauer formula which results in  $\sigma_0 = 4/\pi e^2/h$

A. Ludwig *et al.* PRB 50, 7526 (1994), cond-mat/0610598.

Katsnelson Eur. Phys. J. B **51**, 157 (2006).